

EE3110 - Electronic Devices Laboratory

[EE 3110](#) Electronic Devices Laboratory (1 semester hour) Laboratory to accompany [EE 3310](#). Experimental determination and illustration of properties of carriers in semiconductors including carrier drift, carrier diffusion; p-n junctions including forward and reverse bias effects and transient effects; bipolar transistors including the Ebers-Moll model and secondary effects; field effect transistors including biasing effects, MOS capacitance and threshold voltage. Corequisite: [CE 3310](#) or [EE 3310](#). Prerequisite: [RHET 1302](#). (Same as [CE 3110](#)) (0-1) S